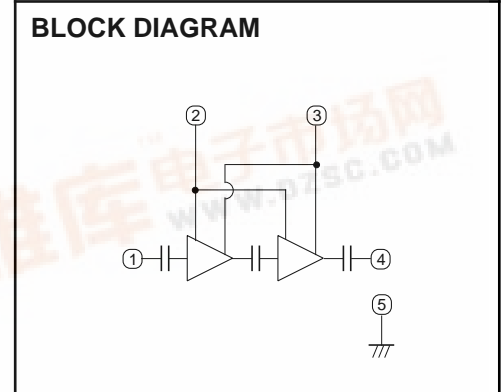
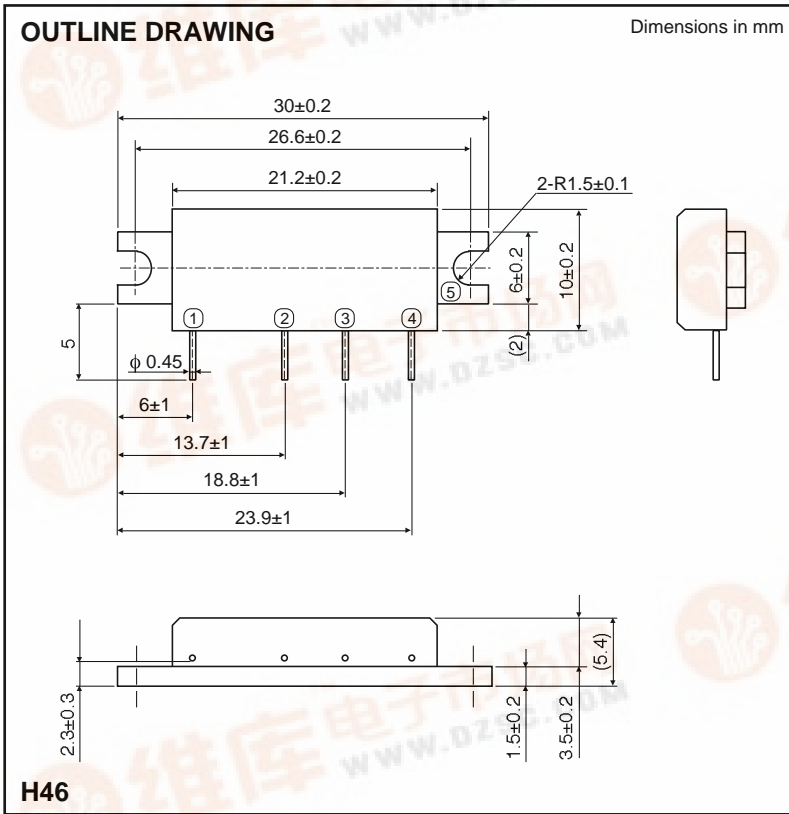


MITSUBISHI RF POWER MODULE

M67799LA

SILICON MOS FET POWER AMPLIFIER, 400-430MHz, 7.5W, FM PORTABLE RADIO



PIN:

- ①Pin : RF INPUT
- ②VGG : GATE BIAS SUPPLY
- ③VDD : DRAIN BIAS SUPPLY
- ④Po : RF OUTPUT
- ⑤GND: FIN

**ABSOLUTE MAXIMUM RATINGS** (Tc=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>DD</sub>	Supply voltage	V <sub>GG</sub> 3.5V, Z <sub>G</sub> =Z <sub>L</sub> =50	16	V
V <sub>GG</sub>	Gate bias voltage		4	V
P <sub>in</sub>	Input power	f=400-430MHz, Z <sub>G</sub> =Z <sub>L</sub> =50	30	mW
P <sub>O</sub>	Output power	f=400-430MHz, Z <sub>G</sub> =Z <sub>L</sub> =50	10	W
T <sub>C (OP)</sub>	Operation case temperature	f=400-430MHz, Z <sub>G</sub> =Z <sub>L</sub> =50	-30 to +100	°C
T <sub>stg</sub>	Storage temperature		-40 to +110	°C

Note. Above parameters are guaranteed independently.

**ELECTRICAL CHARACTERISTICS** (Tc=25°C, Z<sub>G</sub>=Z<sub>L</sub>=50 unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit	
			Min	Max		
f	Frequency range		400	430	MHz	
P <sub>O</sub>	Output power	V <sub>DD</sub> =9.6V, V <sub>GG</sub> =3.5V, P <sub>in</sub> =20mW	7.5		W	
τ	Total efficiency		43		%	
2f <sub>o</sub>	2nd. harmonic			-25		dBc
in	Input VSWR			4		-
-	Stability	Z <sub>G</sub> =50, V <sub>DD</sub> =4.8-13.2V, Load VSWR<4:1	No parasitic oscillation		-	
-	Load VSWR tolerance	V <sub>DD</sub> =13.2V, P <sub>in</sub> =20mW, P <sub>O</sub> =7.5W (V <sub>GG</sub> adjust), Z <sub>L</sub> =20:1	No degradation or destroy		-	

Note. Above parameters, ratings, limits and test conditions are subject to change.

